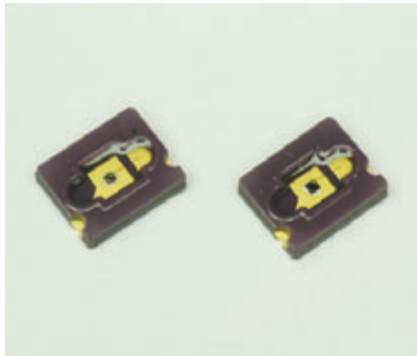


InGaAs PIN photodiodes

G11193 series **25-05805**



Small package, surface mount type

Features

- Small SMD (surface mount device) package
- Low noise, low dark current
- Low price

Applications

- Optical power meter
- Measurement/analytical instruments

General ratings

Parameter	G11193-02R	G11193-03R	Unit
Package	SMD		-
Active area	φ0.2	φ0.3	mm
Window	Resin		-

Absolute maximum ratings

Parameter	Symbol	G11193-02R	G11193-03R	Unit
Reverse voltage	V _R Max.	10		V
Operating temperature	T _{opr}	-25 to +85*		°C
Storage temperature	T _{stg}	-40 to +100*		°C

* No condensation

Electrical and optical characteristics (T_a=25 °C)

Parameter	Symbol	Condition	G11193-02R			G11193-03R			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range	λ	Higher than 10% of peak	-	0.9 to 1.7	-	-	0.9 to 1.7	-	μm
Peak sensitivity wavelength	λ _p		-	1.55	-	-	1.55	-	μm
Photo sensitivity	S	λ=1.3 μm λ=1.55 μm	0.75 0.77	0.85 1.0	- -	0.75 0.77	0.85 1.0	- -	A/W
Dark current	I _D	V _R =5 V	-	40	800	-	100	1200	pA
Cut-off frequency	f _c	V _R =5 V, R _L =50 Ω	-	1	-	-	0.5	-	GHz
Terminal capacitance	C _t	V _R =5 V, f=1 MHz	-	3	-	-	5	-	pF
Shunt resistance	R _{sh}	V _R =10 mV	-	1000	-	-	700	-	MΩ
Detectivity	D*	λ=λ _p	-	5 × 10 ¹²	-	-	5 × 10 ¹²	-	cm·Hz ^{1/2} /W

Spectral response

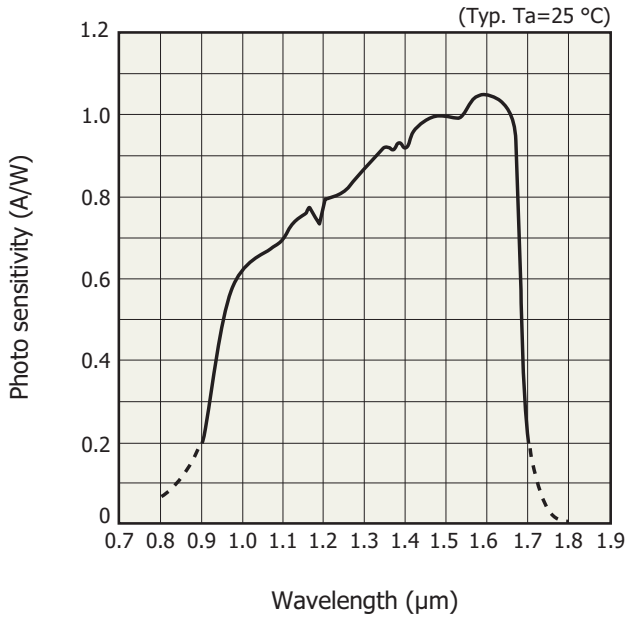
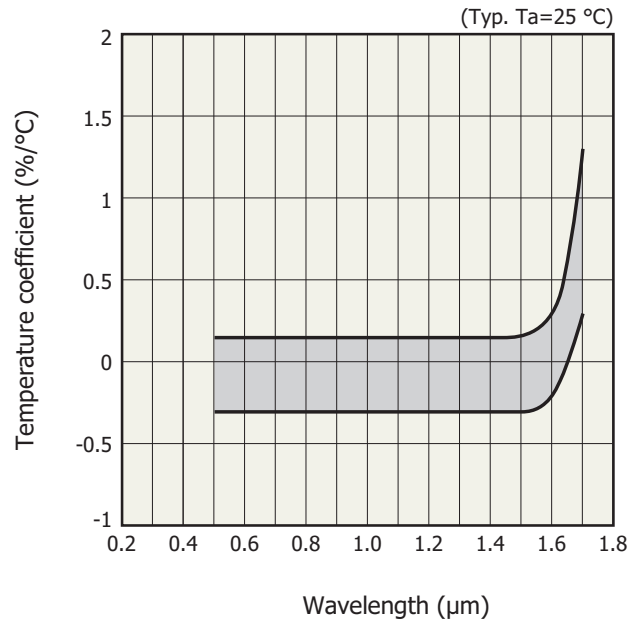
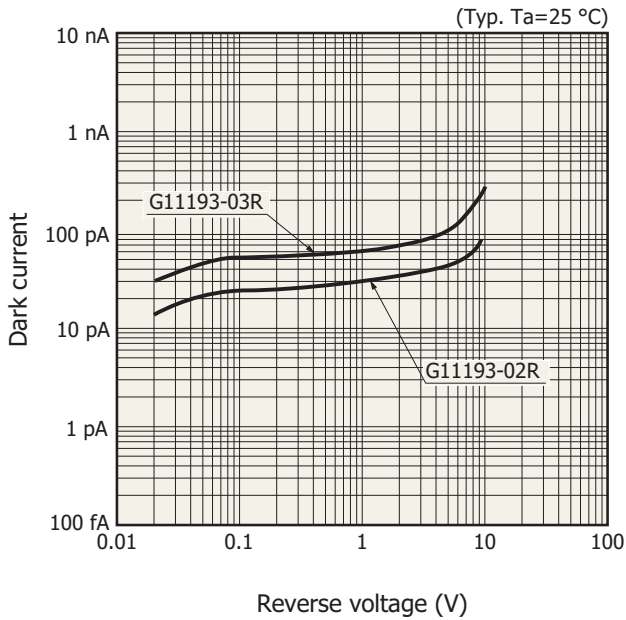


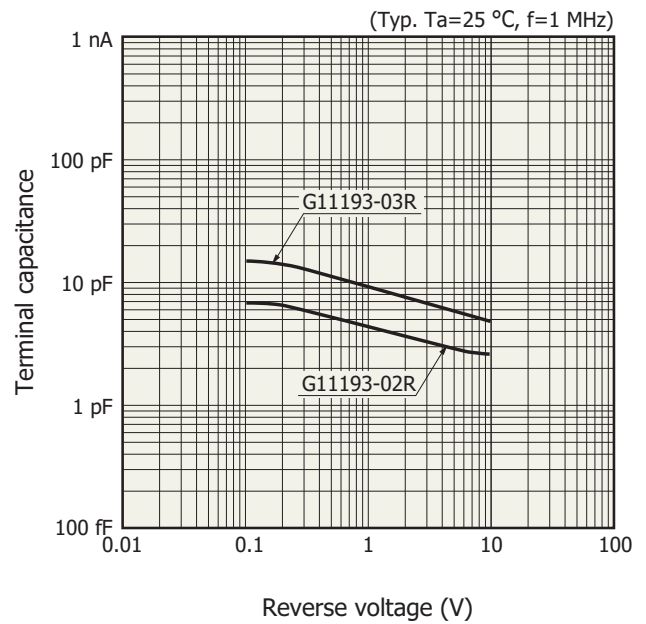
Photo sensitivity temperature characteristic

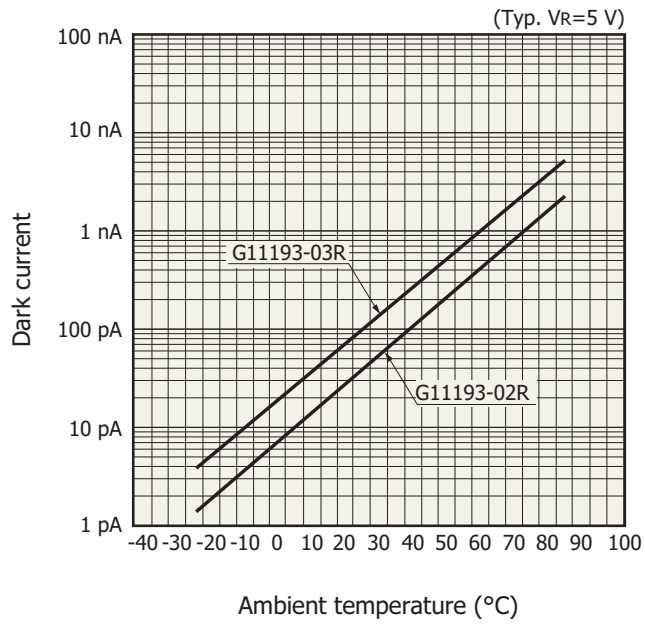


Dark current vs. reverse voltage

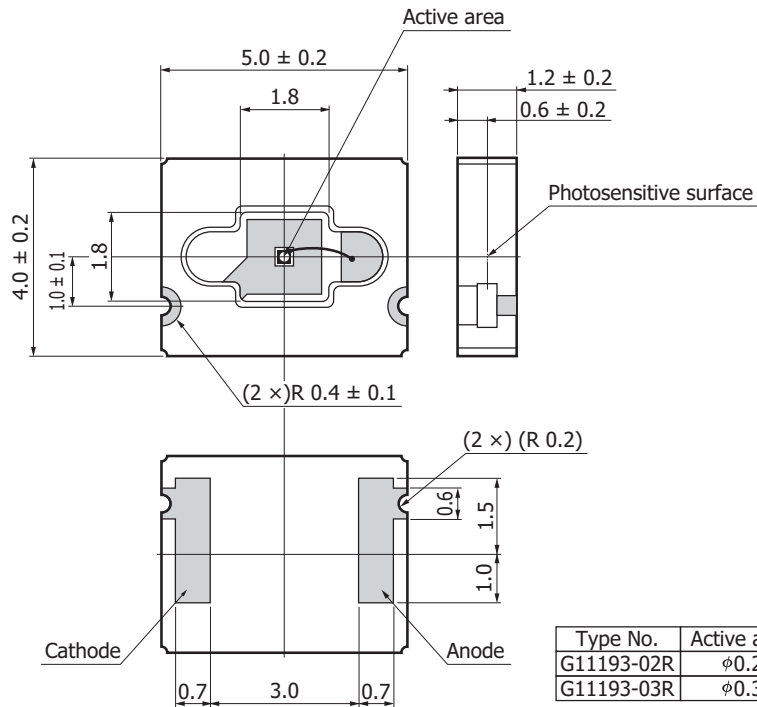


Terminal capacitance vs. reverse voltage



Dark current vs. ambient temperature

Dimensional outline (unit: mm)



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Information furnished by HAMAMATSU is believed to be reliable. However, no responsibility is assumed for possible inaccuracies or omissions.

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Type numbers of products listed in the specification sheets or supplied as samples may have a suffix "(X)" which means tentative specifications or a suffix "(Z)" which means developmental specifications. ©2010 Hamamatsu Photonics K.K.

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 8152-375-0, Fax: (49) 8152-265-8

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1 int. 6, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741